

## 30V N-CHANNEL Enhancement Mode MOSFET

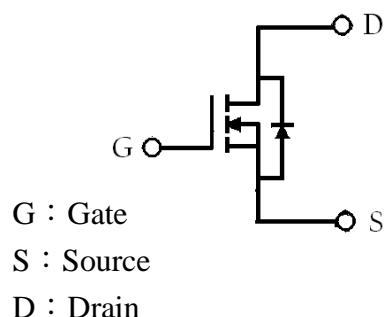
### Features:

- Low on-resistance
- Low gate charge
- Excellent thermal and electrical capabilities
- Compact and low profile SOT-23 package
- Pb-free lead plating and halogen-free package

SOT-23



<b>BV<sub>DSS</sub></b>		30V
ID@V <sub>GS</sub> =10V, T <sub>A</sub> =25°C		5.8A
<b>R<sub>DSON(TYP)</sub></b>	V <sub>GS</sub> =10V, ID=5.8A	20mΩ
	V <sub>GS</sub> =4.5V, ID=5A	22mΩ
	V <sub>GS</sub> =2.5V, ID=4A	27mΩ



### Ordering Information

Device	Package	Shipping
KW3400N3	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel

## Absolute Maximum Ratings ( $T_a=25^\circ C$ )

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	
Continuous Drain Current @ $T_A=25^\circ C$ , $V_{GS}=10V$ (Note 3)	$I_D$	5.8	A
Continuous Drain Current @ $T_A=70^\circ C$ , $V_{GS}=10V$ (Note 3)		4.6	
Pulsed Drain Current (Note 1, 2)	$I_{DM}$	30	
Maximum Power Dissipation @ $T_A=25^\circ C$	$P_D$	1.38	W
Linear Derating Factor		0.01	W/ $^\circ C$
Operating Junction and Storage Temperature	$T_j, T_{stg}$	-55~+150	$^\circ C$

Note : 1. Pulse width limited by maximum junction temperature.  
 2. Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .

## Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction-to-Ambient, max (Note)	$R_{\theta JA}$	90	$^\circ C/W$
Thermal Resistance, Junction-to-Case, max	$R_{\theta JC}$	75	

Note : Surface mounted on 1 in<sup>2</sup> copper pad of FR-4 board,  $t \leq 5s$ ; 270°C/W when mounted on minimum copper pad.

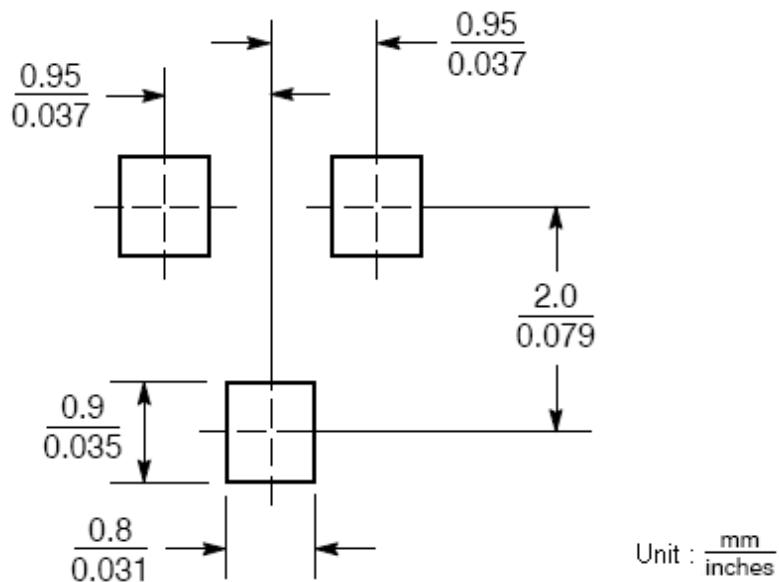
## Electrical Characteristics ( $T_a=25^\circ C$ )

Symbol	Min.	Typ.	Max.	Unit	Test Conditions	
<b>Static</b>						
$BV_{DSS}$	30	-	-	V	$V_{GS}=0V, I_D=250\mu A$	
$V_{GS(th)}$	0.7	-	1.4		$V_{DS}=V_{GS}, I_D=250\mu A$	
$G_{FS}$	-	11	-	S	$V_{DS}=5V, I_D=5A$	
$I_{GSS}$	-	-	$\pm 100$	nA	$V_{GS}=\pm 12V, V_{DS}=0V$	
$I_{DSS}$	-	-	1	$\mu A$	$V_{DS}=24V, V_{GS}=0V$	
$I_{DSR}$	-	-	5		$V_{DS}=24V, V_{GS}=0V, T_j=55^\circ C$	
$*R_{DS(ON)}$	-	20	26	$m \curvearrowright$	$V_{GS}=10V, I_D=5.8A$	
	-	22	30		$V_{GS}=4.5V, I_D=5A$	
	-	27	52		$V_{GS}=2.5V, I_D=4A$	
<b>Dynamic</b>						
$C_{iss}$	-	640	-	pF	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	
$C_{oss}$	-	64	-			
$C_{rss}$	-	53	-			
$*t_{d(ON)}$	-	4.6	-	ns	$V_{DS}=15V, V_{GS}=10V, R_G=3\Omega, I_D=5.8A$	
$*t_r$	-	13.6	-			
$*t_{d(OFF)}$	-	36.8	-			
$*t_f$	-	4.4	-			

*Qg	-	7.8	12	nC	V <sub>DS</sub> =15V, I <sub>D</sub> =5.8A, V <sub>GS</sub> =4.5V
*Qgs	-	1.4	-		
*Qgd	-	1.7	-		
R <sub>g</sub>	-	4.6	-	∞	f=1MHz
<b>Source-Drain Diode</b>					
*V <sub>SD</sub>	-	0.75	1.0	V	V <sub>GS</sub> =0V, I <sub>S</sub> =1.0A
*I <sub>S</sub>	-	-	2.5	A	V <sub>D</sub> =V <sub>G</sub> =0V, V <sub>S</sub> =1.0V
*t <sub>rr</sub>	-	7.8	-	ns	Is=5A, V <sub>GS</sub> =0V, dI/dt=100A/μs
*Q <sub>rr</sub>	-	3.9	-	nC	

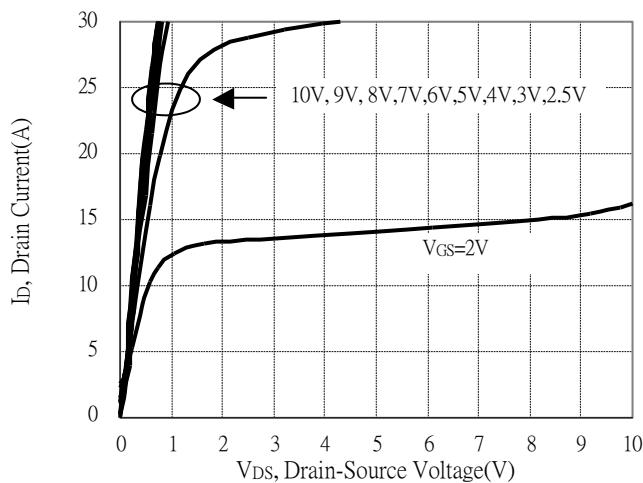
\*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

### Recommended Soldering Footprint

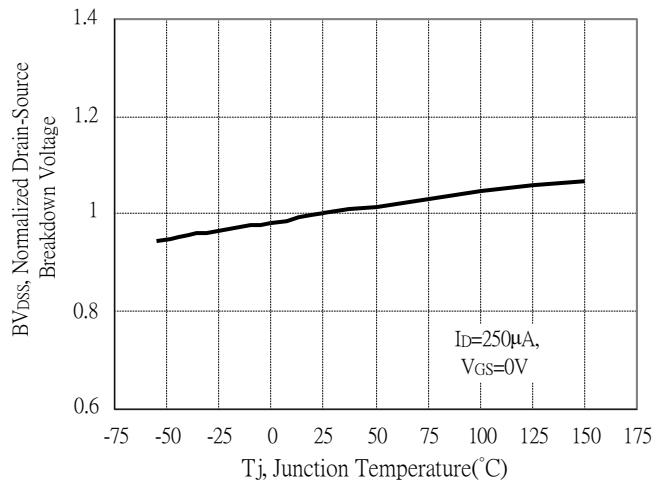


## Typical Characteristics

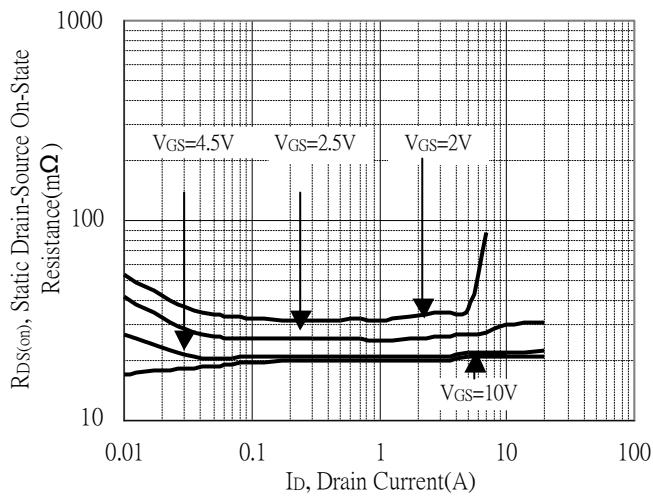
Typical Output Characteristics



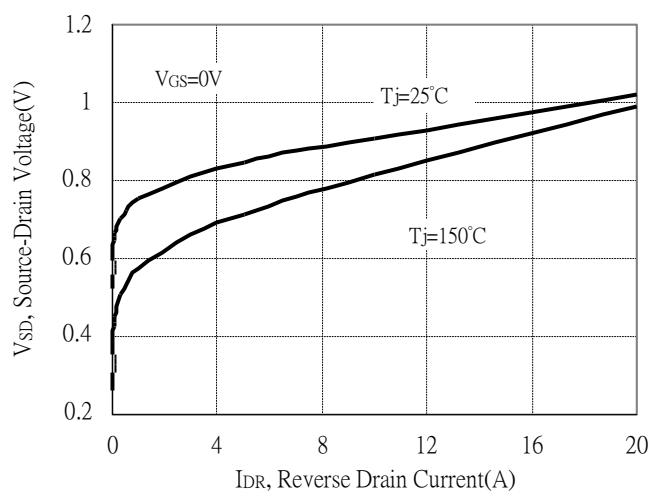
Breakdown Voltage vs Ambient Temperature



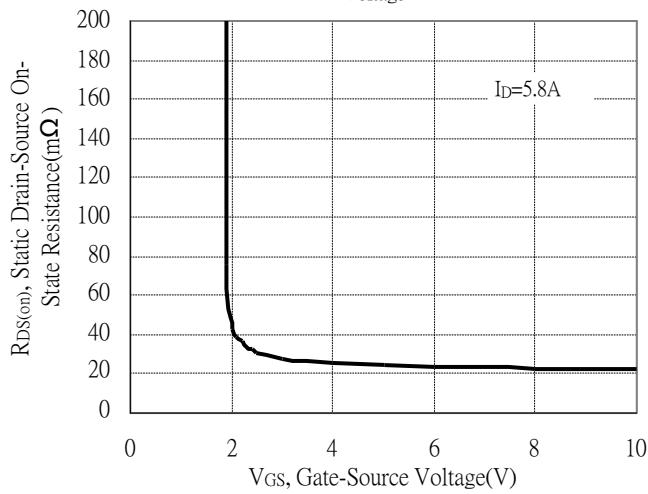
Static Drain-Source On-State resistance vs Drain Current



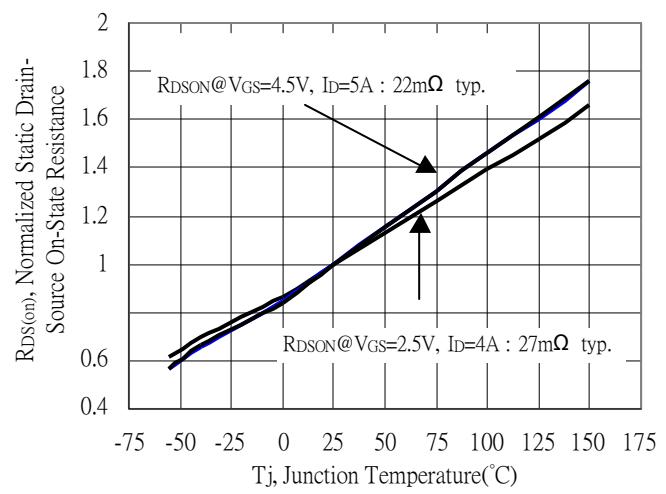
Reverse Drain Current vs Source-Drain Voltage



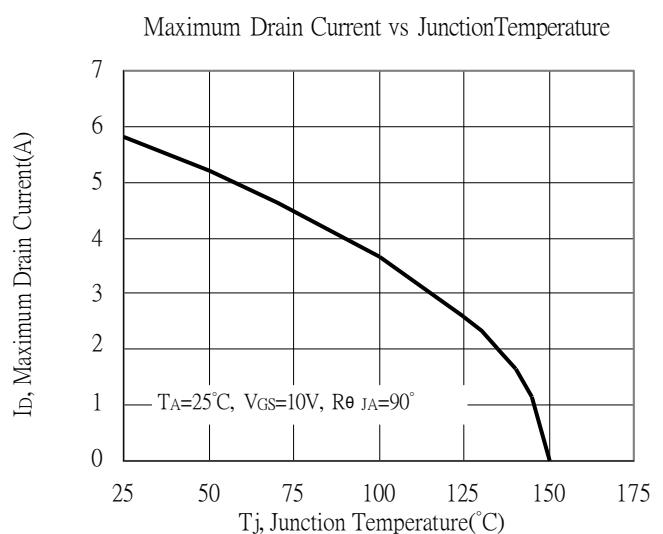
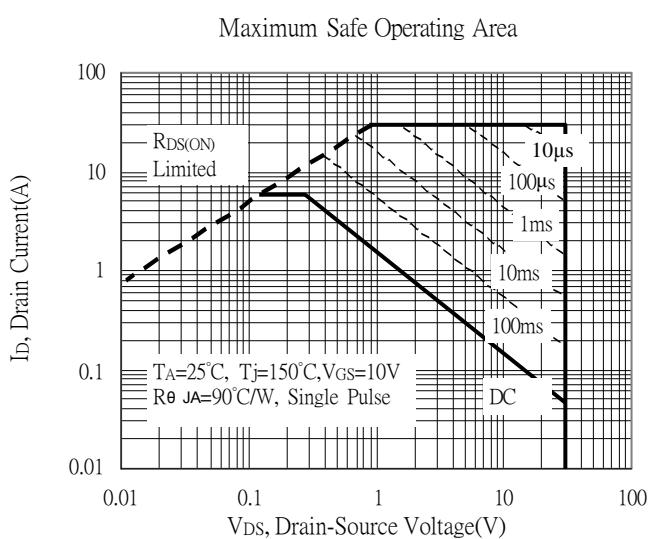
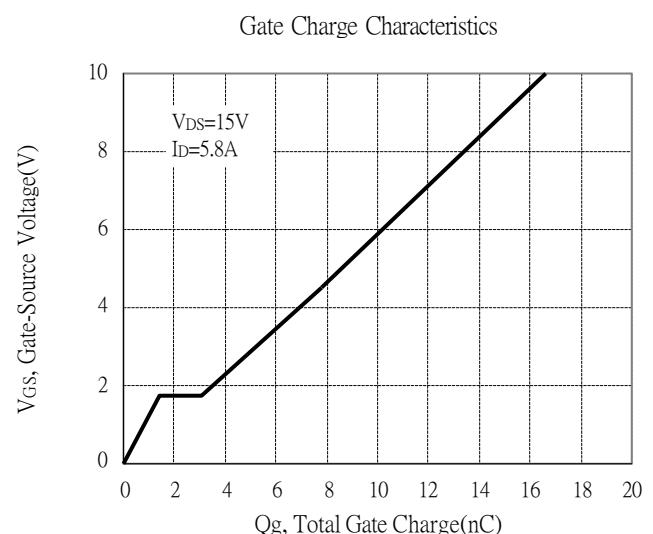
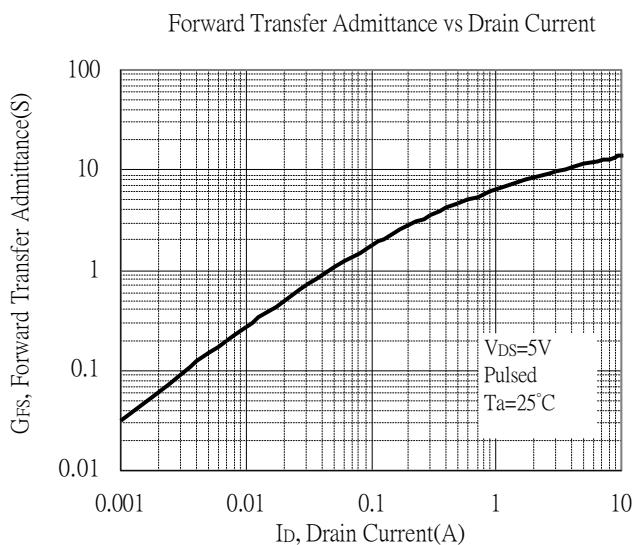
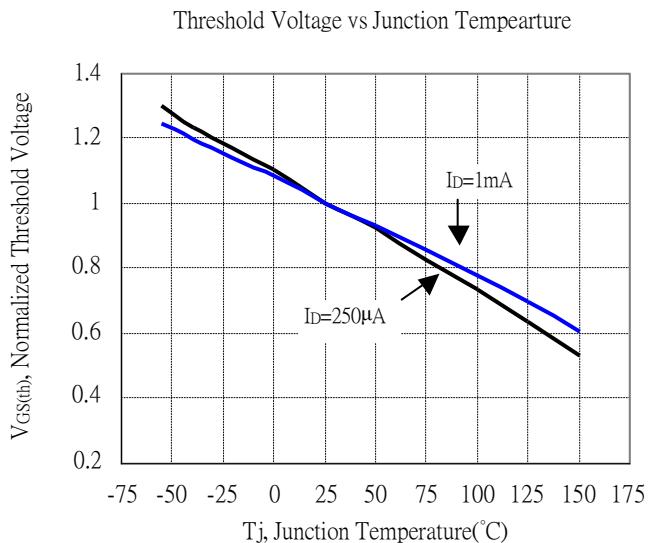
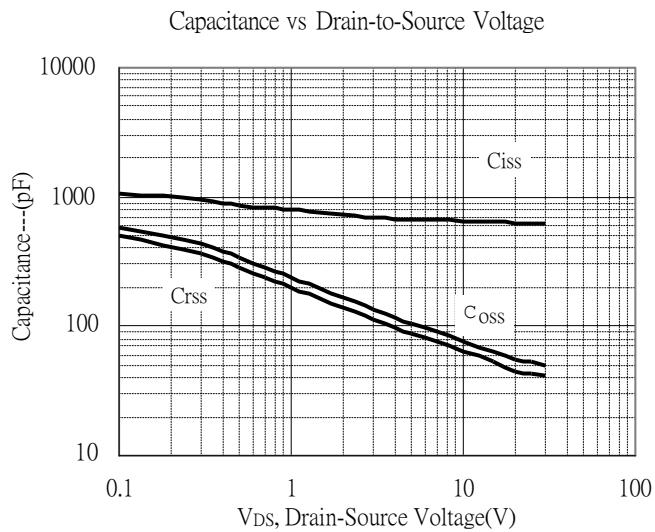
Static Drain-Source On-State Resistance vs Gate-Source Voltage



Drain-Source On-State Resistance vs Junction Temperature

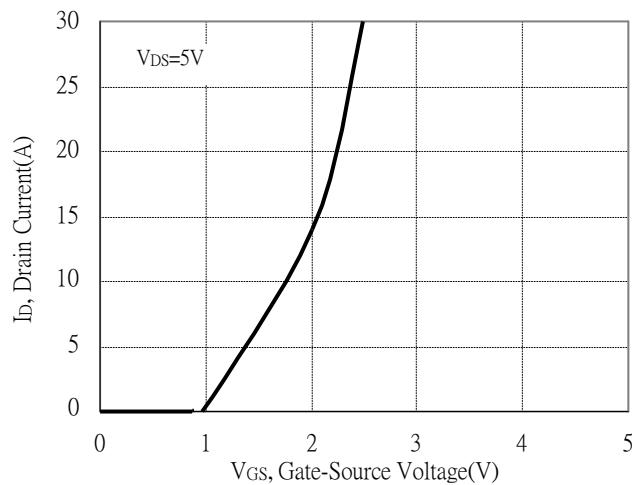


## Typical Characteristics(Cont.)

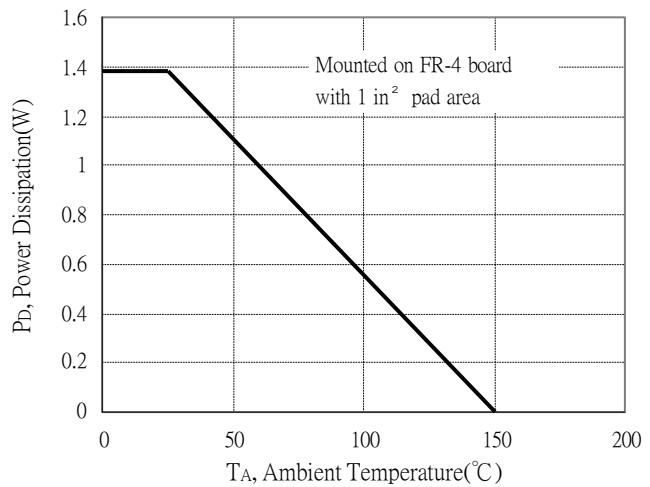


## Typical Characteristics(Cont.)

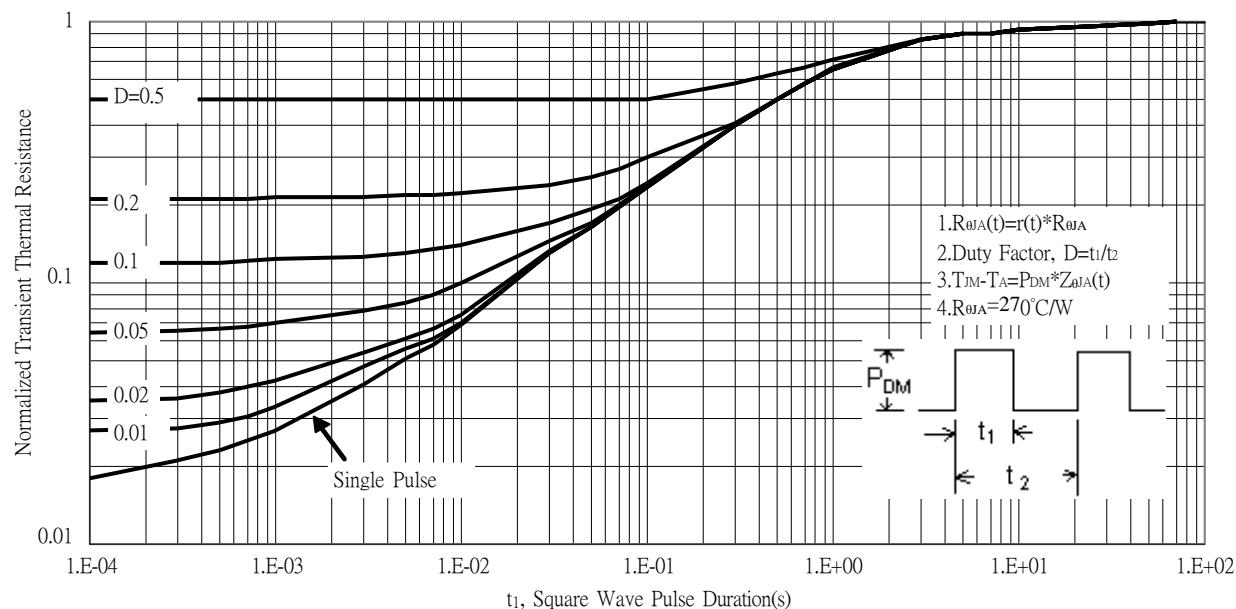
Typical Transfer Characteristics



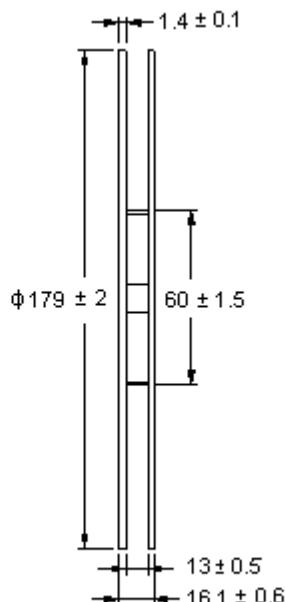
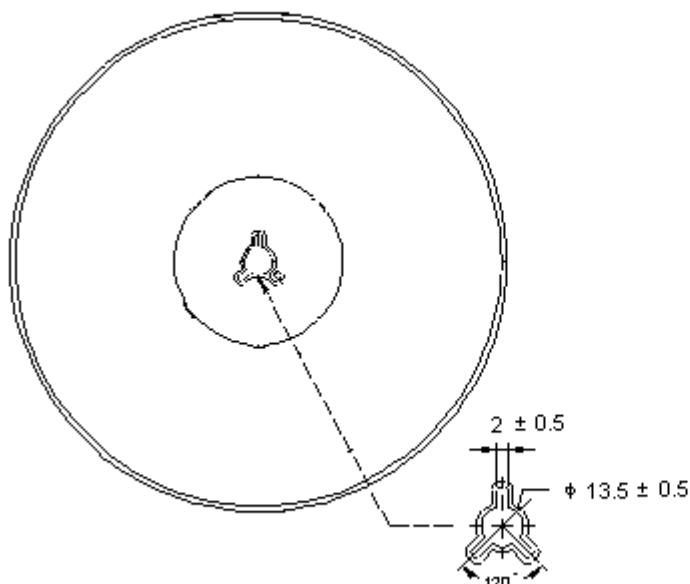
Power Derating Curve



Transient Thermal Response Curves

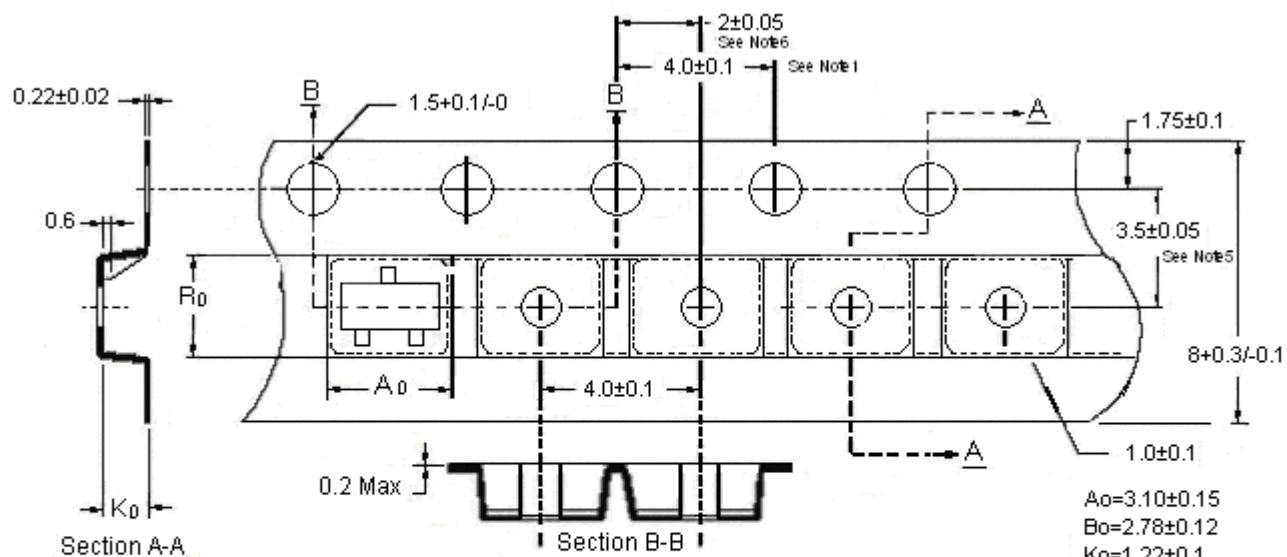


## Reel Dimension



Unit: millimeter

## Carrier Tape Dimension

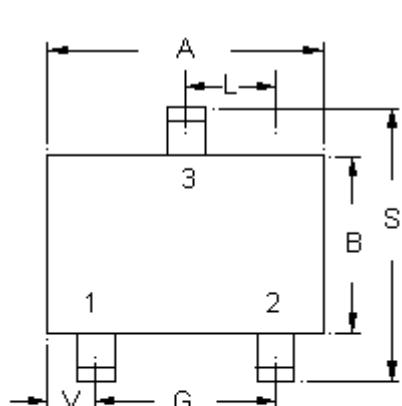


Notes:

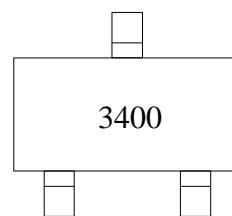
1. 10 sprocket hole pitch cumulative tolerance  $\pm 0.2$ .
2. Camber not to exceed 1mm in 100mm.
3. Material : conductive Black Polystyrene.
4.  $A_0$  &  $B_0$  measured on a plane 0.3mm above the bottom of the pocket.
5.  $K_0$  measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Unit : millimeter

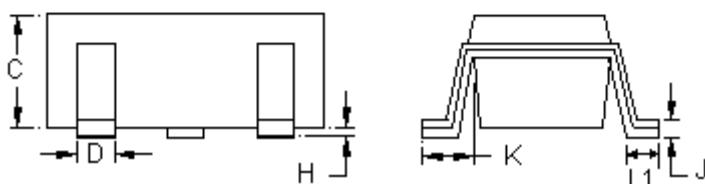
## SOT-23 Dimension



Marking:



3-Lead SOT-23 Plastic  
Surface Mounted Package  
Package Code: N3



Style: Pin 1.Gate 2.Source 3.Drain

\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0032	0.0079	0.08	0.20
B	0.0472	0.0669	1.20	1.70	K	0.0118	0.0266	0.30	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1161	2.10	2.95
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0000	0.0040	0.00	0.10	L1	0.0118	0.0197	0.30	0.50